



LCP1511D

Application Specific Discretes
A.S.D.TM

PROGRAMMABLE TRANSIENT VOLTAGE SUPPRESSOR FOR SLIC PROTECTION

FEATURES

- DUAL PROGRAMMABLE TRANSIENT SUPPRESSOR.
- WIDE NEGATIVE FIRING VOLTAGE RANGE :
 $V_{MGL} = -80V$ max.
- LOW DYNAMIC SWITCHING VOLTAGES :
 V_{FP} and V_{DGL} .
- LOW GATE TRIGGERING CURRENT :
 $I_{GT} = 5mA$ max.
- PEAK PULSE CURRENT :
 $I_{PP} = 30A$ for 10/100 μs surge.
- HOLDING CURRENT :
 $I_H = 150mA$.

DESCRIPTION

This device has been especially designed to protect subscriber line card interfaces (SLIC) against transient overvoltages.

Positive overloads are clipped with 2 diodes. Negative surges are suppressed by 2 thyristors, their breakdown voltage being referenced to $-V_{BAT}$ through the gate.

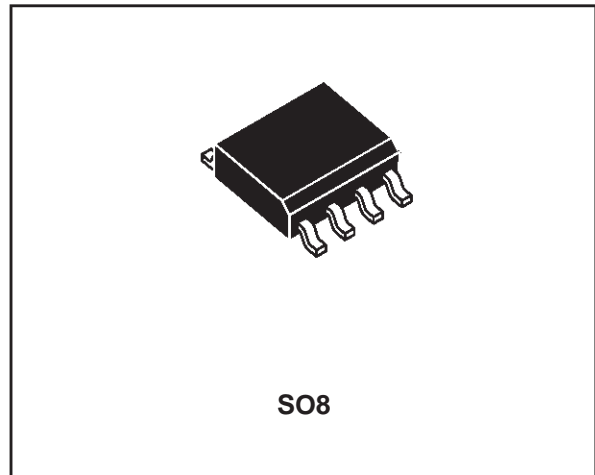
This component presents a very low gate triggering current (I_{GT}) in order to reduce the current consumption on printed circuit board during the firing phase.

A particular attention has been given to the internal wire bonding. The "4-point" configuration ensures reliable protection, eliminating the overvoltage introduced by the parasitic inductances of the wiring (Ldi/dt), especially for very fast transients.

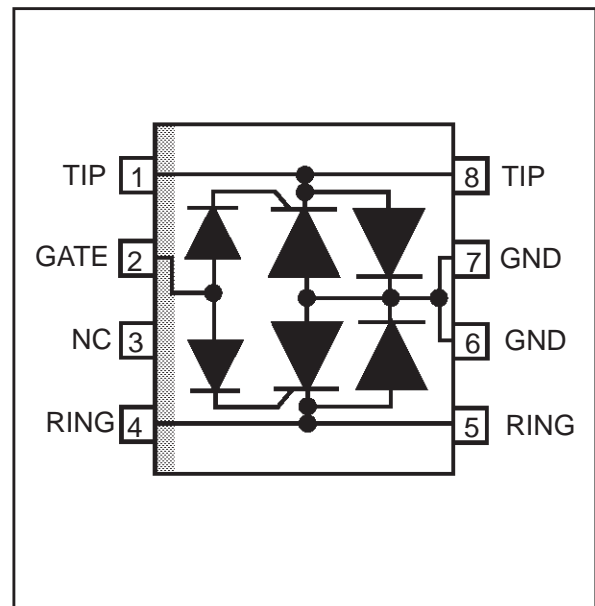
COMPLIES WITH THE FOLLOWING STANDARDS :

CCITT K20 :	10/700 μs	1kV
	5/310 μs	25A
VDE 0433 :	10/700 μs	2kV
	5/310 μs	38A (*)
VDE 0878 :	1.2/50 μs	1.5kV
	1/20 μs	40A
I3124 :	0.5/700 μs	1kV
	0.2/310 μs	25A
FCC part 68 :	2/10 μs	2.5kV
	2/10 μs	170A (*)
BELLCORE		
TR-NWT-001089 :	2/10 μs	2.5kV
	2/10 μs	170A (*)

(*) with series resistors or PTC.



SCHEMATIC DIAGRAM



TM: ASD is trademarks of SGS-THOMSON Microelectronics.

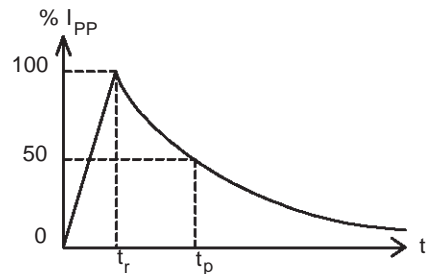
LCP1511D

ABSOLUTE MAXIMUM RATINGS (T_{amb} = 25 °C)

Symbol	Parameter	Value	Unit
I _{PP}	Peak pulse current (see note 1)	10/1000µs 5/310µs 2/10µs	30 38 170 A
I _{TSM}	Non repetitive surge peak on-state current (F = 50Hz)	t _p = 10ms t = 1s	8 3.5 A
I _{GSM}	Maximum gate current (half sine wave t _p = 10ms)		2 A
V _{MLG} V _{MGL}	Maximum voltage LINE / GROUND Maximum voltage GATE / LINE		-100 -80 V
T _{stg} T _j	Storage temperature range Maximum junction temperature		- 55 to + 150 150 °C
T _L	Maximum lead temperature for soldering during 10s		260 °C

Note 1 : Pulse waveform :

10/1000µs	t _r =10µs	t _p =1000µs
5/310µs	t _r =5µs	t _p =310µs
2/10µs	t _r =2µs	t _p =10µs

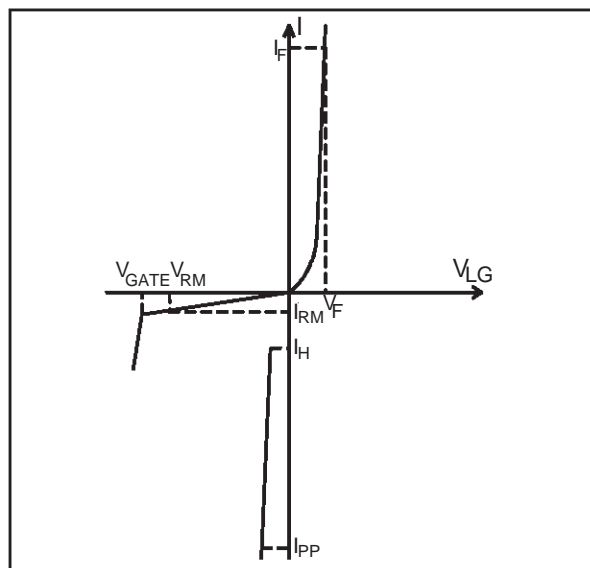


THERMAL RESISTANCE

Symbol	Parameter	Value	Unit
R _{th(j-a)}	Junction to ambient	170	°C/W

ELECTRICAL CHARACTERISTICS (T_{amb} = 25 °C)

Symbol	Parameter
I _{GT}	Gate triggering current
I _H	Holding current
I _{RM}	Reverse leakage current LINE/GND
I _{RG}	Reverse leakage current GATE/LINE
V _{RM}	Reverse voltage LINE/GND
V _F	Forward drop voltage LINE/GND
V _{GT}	Gate triggering voltage
V _{FP}	Peak forward voltage LINE/GND
V _{DGL}	Dynamic switching voltage GATE/LINE
V _{GATE}	GATE/GND voltage
V _{LG}	LINE/GND voltage
C	Off-state capacitance LINE/GND



1 - PARAMETERS RELATED TO THE DIODE LINE/GND ($T_{amb} = 25\text{ }^{\circ}\text{C}$)

Symbol	Test conditions	Maximum	Unit
V_F	$I_F=5\text{A}$ $t_p=500\mu\text{s}$	3	V
V_{FP}	$10/700\mu\text{s}$ 1.5kV $R_p=10\Omega$ $1.2/50\mu\text{s}$ 1.5kV $R_p=10\Omega$ (see note 1) $2/10\mu\text{s}$ 2.5kV $R_p=62\Omega$	5 7 12	V

Note 1 : See test circuit 2 for V_{FP} ; R_p is the protection resistor located on the line card.

2 - PARAMETERS RELATED TO THE PROTECTION THYRISTOR ($T_{amb} = 25\text{ }^{\circ}\text{C}$)

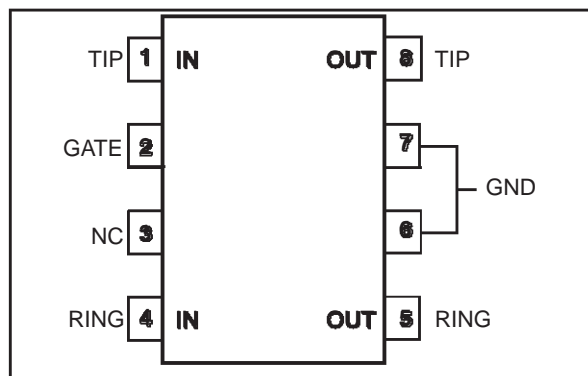
Symbol	Test conditions	Min.	Max.	Unit
I_{GT}	$V_{GND/LINE} = -48\text{V}$	0.2	5	mA
I_H	$V_{GATE} = -48\text{V}$ (see note 2)	150		mA
V_{GT}	at I_{GT}		2.5	V
I_{RG}	$T_c=25\text{ }^{\circ}\text{C}$ $V_{RG} = -75\text{V}$ $T_c=70\text{ }^{\circ}\text{C}$ $V_{RG} = -75\text{V}$		5 50	μA
V_{DGL}	$V_{GATE} = -48\text{V}$ (see note 3) $10/700\mu\text{s}$ 1.5kV $R_p=10\Omega$ $I_{PP}=30\text{A}$ $1.2/50\mu\text{s}$ 1.5kV $R_p=10\Omega$ $I_{PP}=30\text{A}$ $2/10\mu\text{s}$ 2.5kV $R_p=62\Omega$ $I_{PP}=38\text{A}$		10 20 25	V

Note 2 : See the functional holding current (I_H) test circuit 2.

Note 3 : See test circuit 1 for V_{DGL} .
The oscillations with a time duration lower than 50ns are not taken into account.

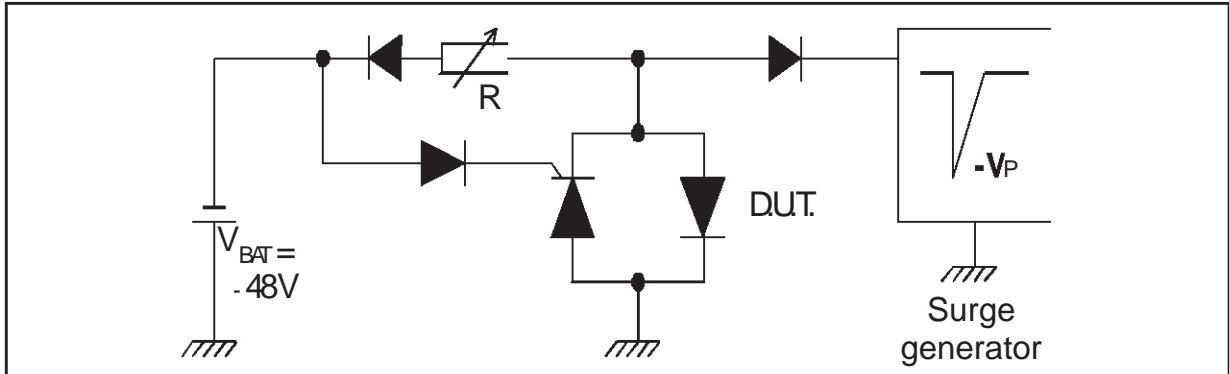
3 - PARAMETERS RELATED TO DIODE AND PROTECTION THYRISTOR ($T_{amb} = 25\text{ }^{\circ}\text{C}$)

Symbol	Test conditions	Maximum	Unit
I_{RM}	$T_c=25\text{ }^{\circ}\text{C}$ $V_{GATE/LINE} = -1\text{V}$ $V_{RM} = -75\text{V}$ $T_c=70\text{ }^{\circ}\text{C}$ $V_{GATE/LINE} = -1\text{V}$ $V_{RM} = -75\text{V}$	5 50	μA
C	$V_R = -3\text{V}$ $F=1\text{MHz}$ $V_R = -48\text{V}$ $F=1\text{MHz}$	100 50	pF

APPLICATION NOTE

In order to take advantage of the "4 point" structure of the LCP, the TIP and RING lines go across the device. In such case, the device will eliminate the overvoltages generated by the parasitic inductances of the wiring (Ldi/dt), especially for very fast transients.

FUNCTIONAL HOLDING CURRENT (I_H) TEST CIRCUIT 1 : GO-NO GO TEST

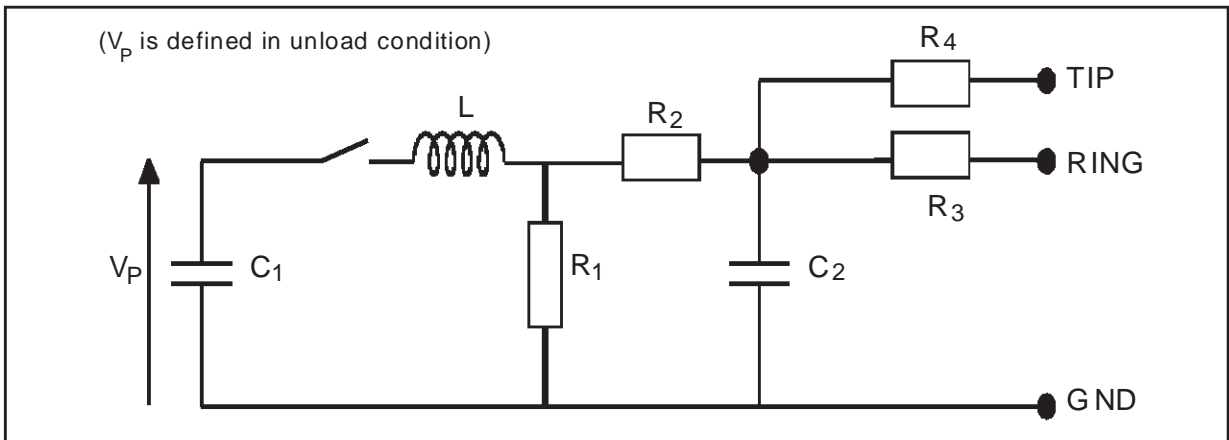


This is a GO-NO GO test which allows to confirm the holding current (I_H) level in a functional test circuit.

TEST PROCEDURE :

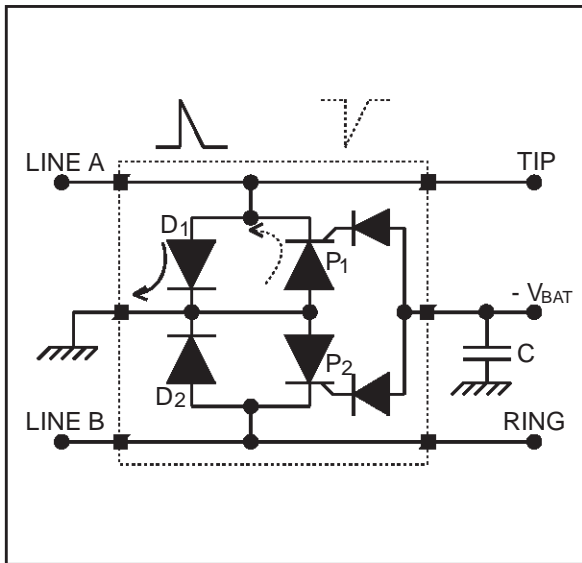
- Adjust the current level at the I_H value by short circuiting the D.U.T.
- Fire the D.U.T. with a surge current : $I_{PP} = 10A, 10/1000\mu s$.
- The D.U.T. will come back to the off-state within a duration of 50ms max.

TEST CIRCUIT 2 FOR V_{FP} AND V_{DGL} PARAMETERS



Pulse (μs)		V_p (V)	C_1 (μF)	C_2 (nF)	L (μH)	R_1 (Ω)	R_2 (Ω)	R_3 (Ω)	R_4 (Ω)	I_{PP} (A)	R_p (Ω)
t_r	t_p										
10	700	1500	20	200	0	50	15	25	25	30	10
1.2	50	1500	1	33	0	76	13	25	25	30	10
2	10	2500	10	0	1.1	1.3	0	3	3	38	62

FUNCTIONAL DESCRIPTION



LINE A PROTECTION :

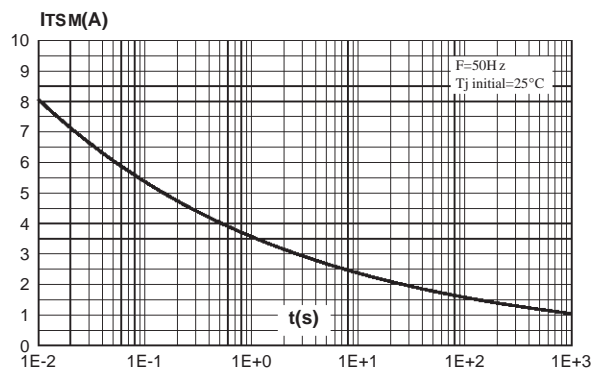
- For positive surges versus GND, the diode D1 will conduct.
- For negative surges versus GND, the protection device P1 will trigger at a voltage fixed by the $-V_{BAT}$ reference.

LINE B PROTECTION :

- For surges on line B, the operating mode is the same, D2 or P2 is activated.

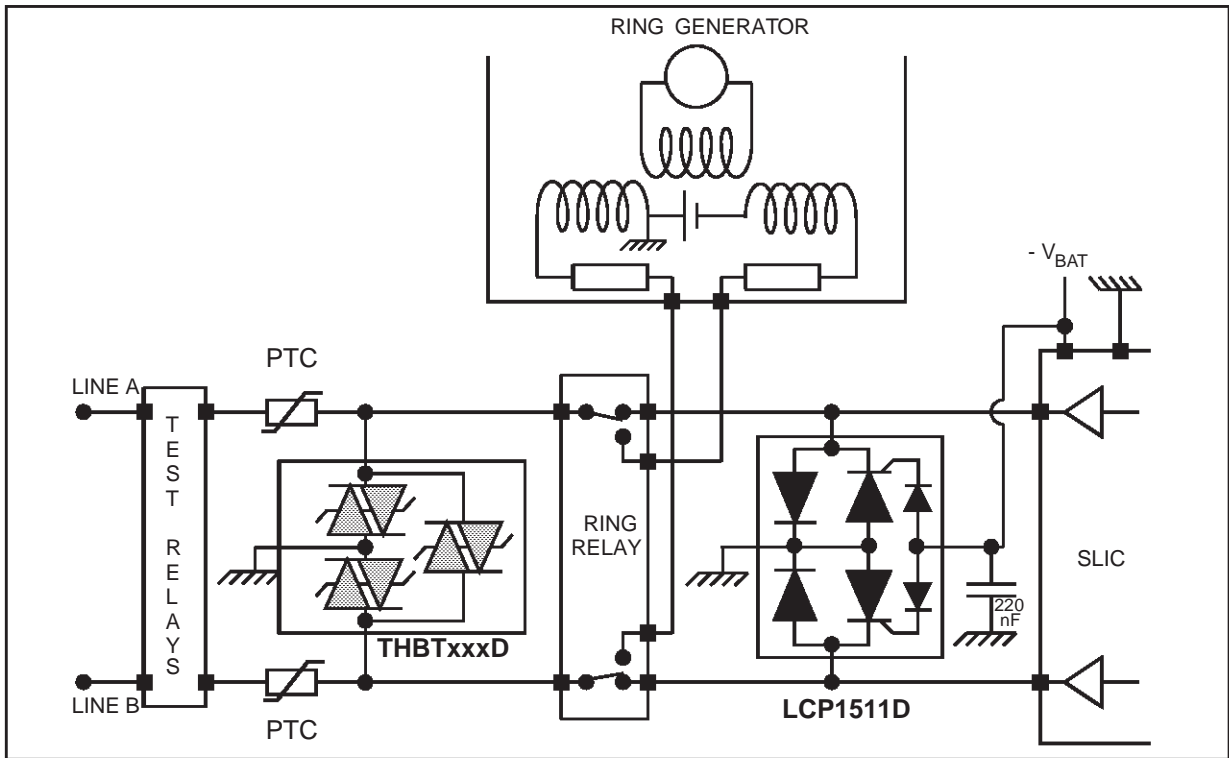
It is recommended to add a capacitor ($C=220\text{nF}$) close to the gate of the LCP, in order to speed up the triggering.

Surge peak current versus overload duration.

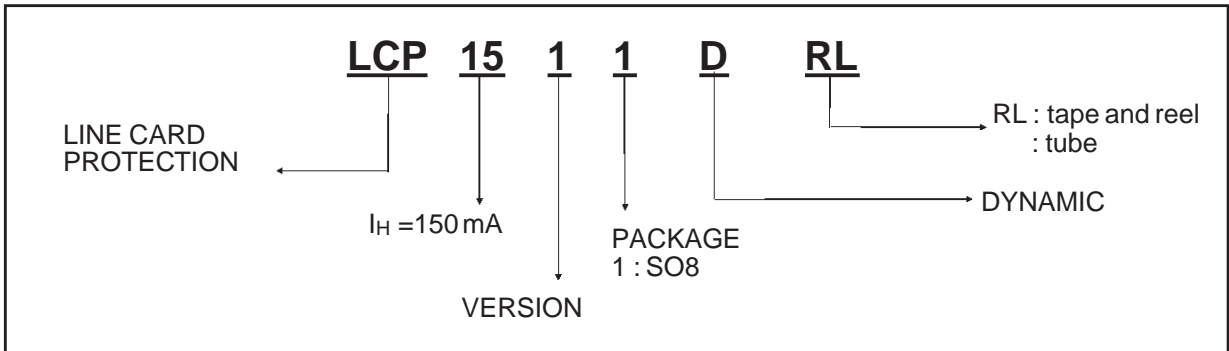


LCP1511D

APPLICATION CIRCUIT : typical SLIC protection concept



ORDER CODE

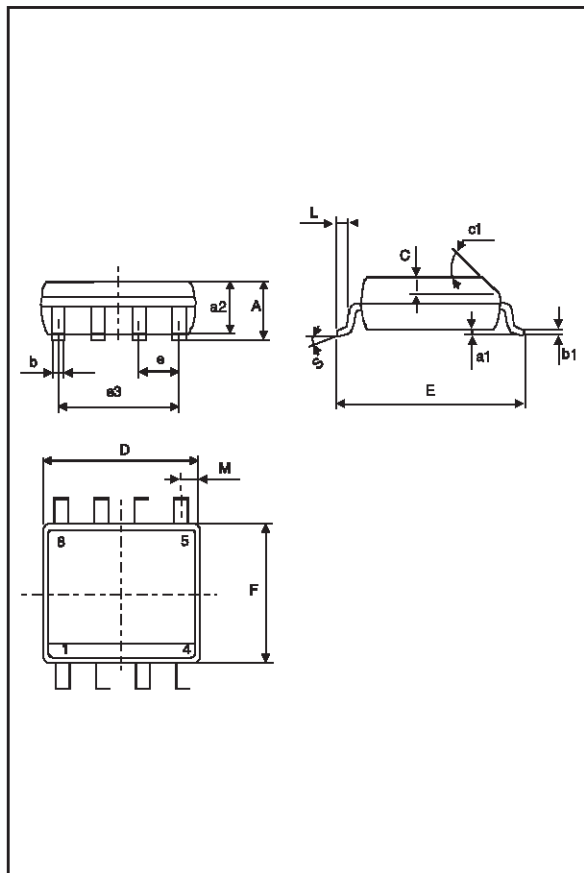


MARKING

Package	Type	Marking
SO8	LCP1511D	CP151D

PACKAGE MECHANICAL DATA

SO8 Plastic



REF.	DIMENSIONS					
	Millimetres			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A			1.75			0.069
a1	0.1		0.25	0.004		0.010
a2			1.65			0.065
b	0.35		0.48	0.014		0.019
b1	0.19		0.25	0.007		0.010
C		0.50			0.020	
c1	45° (typ)					
D	4.8		5.0	0.189		0.197
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		3.81			0.150	
F	3.8		4.0	0.15		0.157
L	0.4		1.27	0.016		0.050
M			0.6			0.024
S	8° (max)					

Weight = 0.08 g.**Packaging:** Product supplied in antistatic tubes or tape and reel.

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

© 1998 STMicroelectronics - Printed in Italy - All rights reserved.

STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - Canada - China - France - Germany - Italy - Japan - Korea - Malaysia - Malta - Mexico - Morocco - The Netherlands - Singapore - Spain - Sweden - Switzerland - Taiwan - Thailand - United Kingdom - U.S.A.